



JCS2N60M (F) B

主要参数 MAIN CHARACTERISTICS

I_D	2.0 A
V_{DSS}	600 V
$R_{dson} (V_{gs}=10V)$	5.0 Ω
Q_g	6.0 nC

用途

- 高频开关电源
- 电子镇流器
- UPS 电源

产品特性

- 低栅极电荷
- 低 C_{rss} (典型值 2.1pF)
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

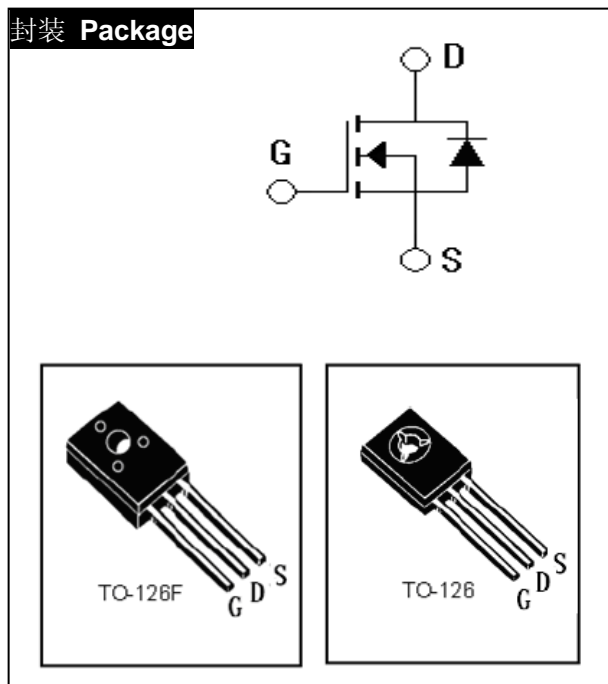
APPLICATIONS

- High efficiency switch mode power supplies
- Electronic lamp ballasts based on half bridge
- UPS

FEATURES

- Low gate charge
- Low C_{rss} (typical 2.1pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订货型号 Order codes	印记 Marking	封装 Package	无卤素 Halogen Free	包装 Packaging
JCS2N60MB-O-F-N-B	JCS2N60MB	TO-126	否 NO	条管 Tube
JCS2N60MFB-O-F-N-B	JCS2N60MFB	TO-126F	否 NO	条管 Tube





绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
		JCS2N60MB/MFB	
最高漏极-源极直流电压 Drain-Source Voltage	V_{DSS}	600	V
连续漏极电流 Drain Current-continuous	I_D T=25°C T=100°C	1.9	A
		1.1	A
最大脉冲漏极电流 (注1) Drain Current – pulse (note 1)	I_{DM}	6.0	A
最高栅源电压 Gate-Source Voltage	V_{GSS}	±30	V
单脉冲雪崩能量 (注2) Single Pulsed Avalanche Energy (note 2)	E_{AS}	120	mJ
雪崩电流 (注1) Avalanche Current (note 1)	I_{AR}	1.9	A
重复雪崩能量 (注1) Repetitive Avalanche Current (note 1)	E_{AR}	4.4	mJ
二极管反向恢复最大电 压变化速率 (注3) Peak Diode Recovery dv/dt (note 3)	dv/dt	4.5	V/ns
耗散功率 Power Dissipation	P_D T _C =25°C -Derate above 25°C	44	W
		0.35	W/ °C
最高结温及存储温度 Operating and Storage Temperature Range	T _J , T _{STG}	-55~+150	°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T _L	300	°C

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature





电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	测试条件 Tests conditions	最大 Min	典型 Typ	最大 Max	单 位 Units
关态特性 Off –Characteristics						
漏—源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	600	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=1mA$, referenced to $25^\circ C$	-	0.6	-	$V/^\circ C$
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=600V, V_{GS}=0V,$ $T_C=25^\circ C$	-	-	10	μA
		$V_{DS}=480V, T_C=125^\circ C$	-	-	100	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D=1A$	-	3.9	5.0	Ω
正向跨导 Forward Transconductance	g_{fs}	$V_{DS} = 40V, I_D=1.0A$ (note 4)	-	2.05	-	S
动态特性 Dynamic Characteristics						
输入电容 Input capacitance	C_{iss}	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$	-	190	230	pF
输出电容 Output capacitance	C_{oss}		-	15	20	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	1.8	2.1	pF





电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	$t_{d(on)}$	$V_{DD}=300V, I_D=2.0A, R_G=25\Omega$ (note 4, 5)	-	7	23	ns
上升时间 Turn-On rise time	t_r		-	23	45	ns
延迟时间 Turn-Off delay time	$t_{d(off)}$		-	22	43	ns
下降时间 Turn-Off Fall time	t_f		-	24	46	ns
栅极电荷总量 Total Gate Charge	Q_g	$V_{DS}=480V,$ $I_D=2.0A$ $V_{GS}=10V$ (note 4, 5)	-	5.3	6	nC
栅-源电荷 Gate-Source charge	Q_{gs}		-	1.8	-	nC
栅-漏电荷 Gate-Drain charge	Q_{gd}		-	1.8	-	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current		I_S	-	-	1.9	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}	-	-	6.0	A
正向压降 Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V,$ $I_S=2.0A$	-	-	1.4	V
反向恢复时间 Reverse recovery time	t_{rr}	$V_{GS}=0V, I_S=2.0A$ $di_F/dt=100A/\mu s$ (note 4)	-	230	-	ns
反向恢复电荷 Reverse recovery charge	Q_{rr}		-	1.0	-	μC

热特性 THERMAL CHARACTERISTIC

项 目 Parameter	符 号 Symbol	最大 Max	单 位 Unit
		JCS2N60MB/MFB	
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	2.87	$^{\circ}C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	110	$^{\circ}C/W$

注释:

- 1: 脉冲宽度由最高结温限制
- 2: $L=56mH, I_{AS}=2.0A, V_{DD}=50V, R_G=25\Omega$, 起始结温 $T_J=25^{\circ}C$
- 3: $I_{SD} \leq 2A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$, 起始结温 $T_J=25^{\circ}C$
- 4: 脉冲测试: 脉冲宽度 $\leq 300\mu s$, 占空比 $\leq 2\%$
- 5: 基本与工作温度无关

Notes:

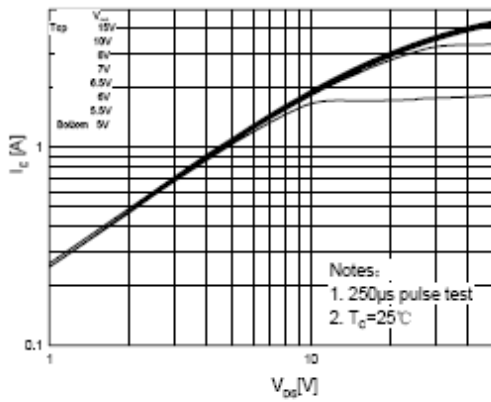
- 1: Pulse width limited by maximum junction temperature
- 2: $L=56mH, I_{AS}=2.0A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^{\circ}C$
- 3: $I_{SD} \leq 2A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
- 5: Essentially independent of operating temperature



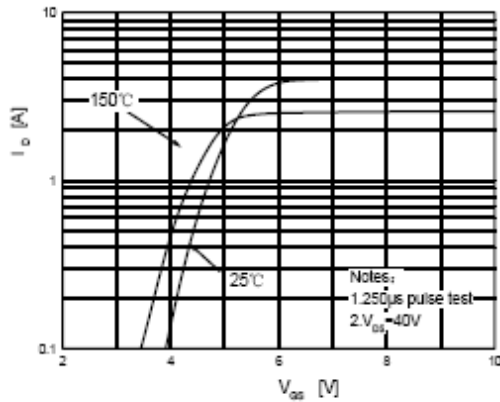


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

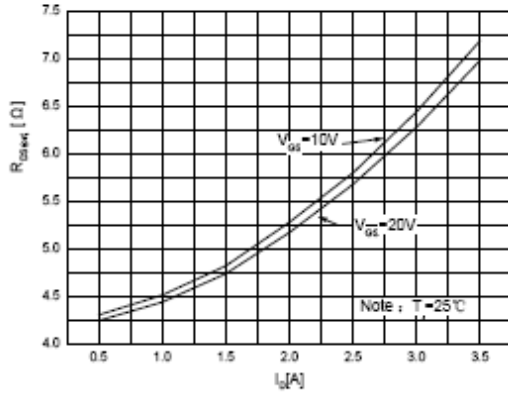
On-Region Characteristics



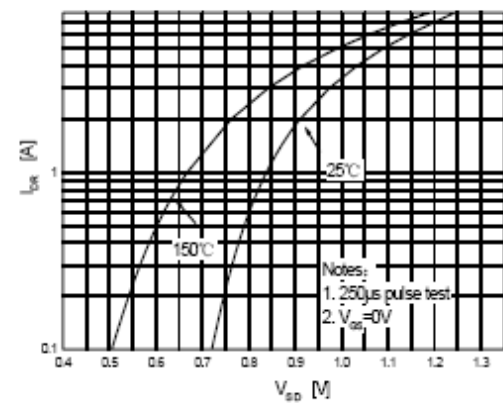
Transfer Characteristics



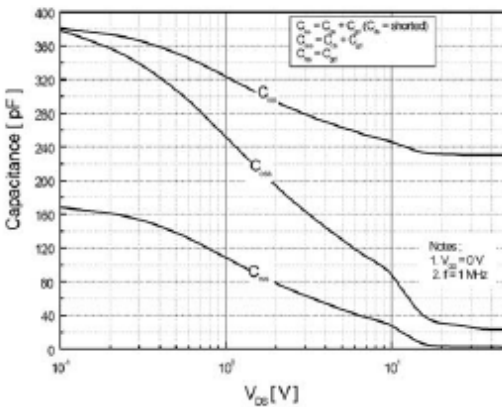
On-Resistance Variation vs. Drain Current and Gate Voltage



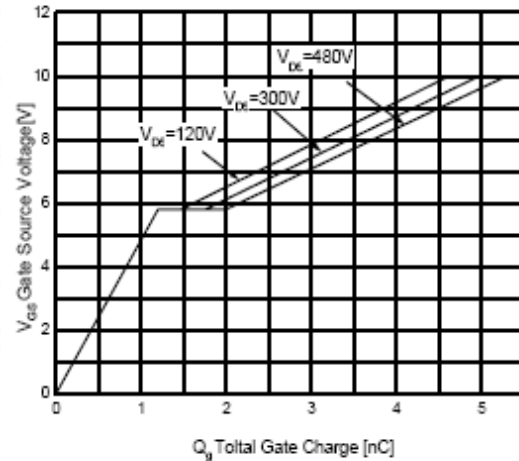
Body Diode Forward Voltage Variation vs. Source Current and Temperature



Capacitance Characteristics



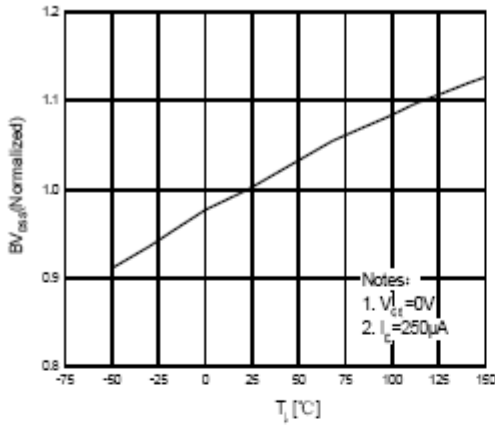
Gate Charge Characteristics



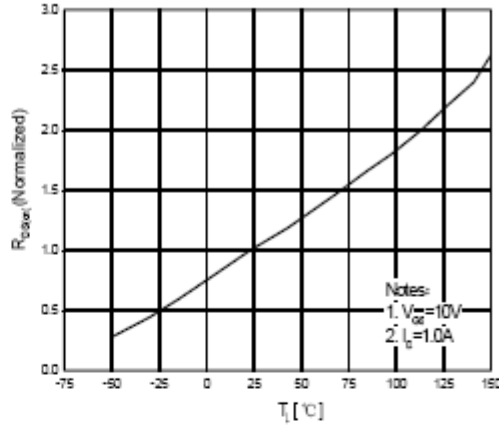


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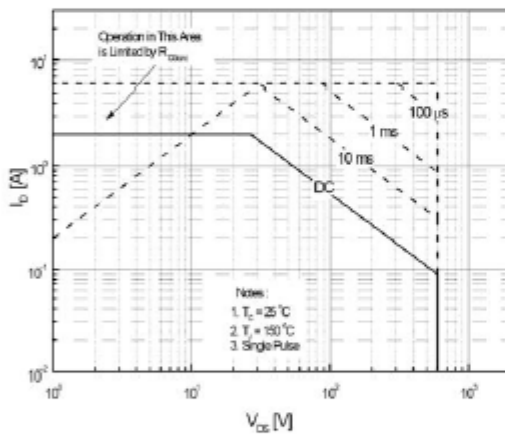
Breakdown Voltage Variation vs. Temperature



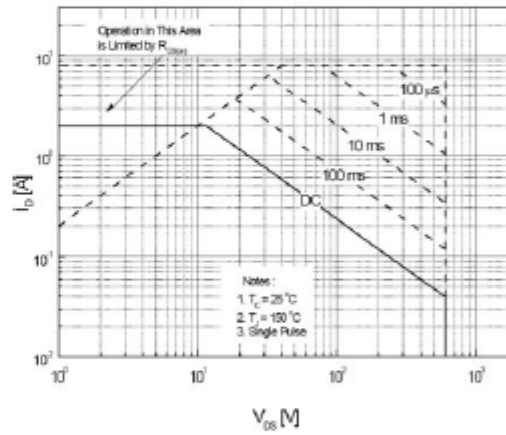
On-Resistance Variation vs. Temperature



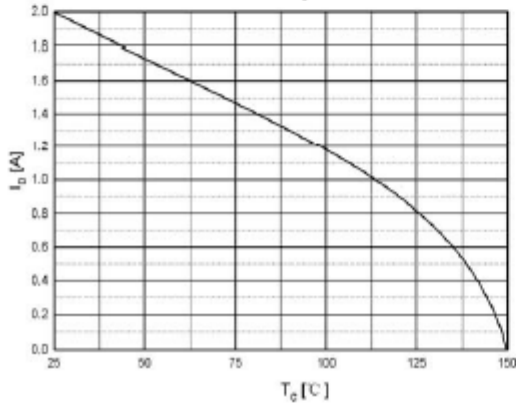
Maximum Safe Operating Area For JCS2N60MB/MFB



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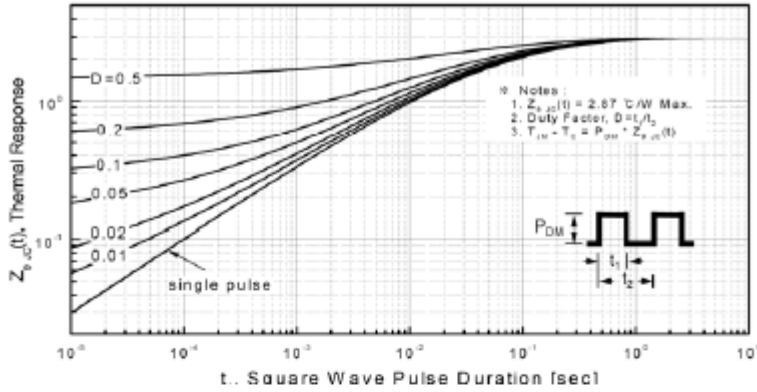
Maximum Drain Current vs. Case Temperature



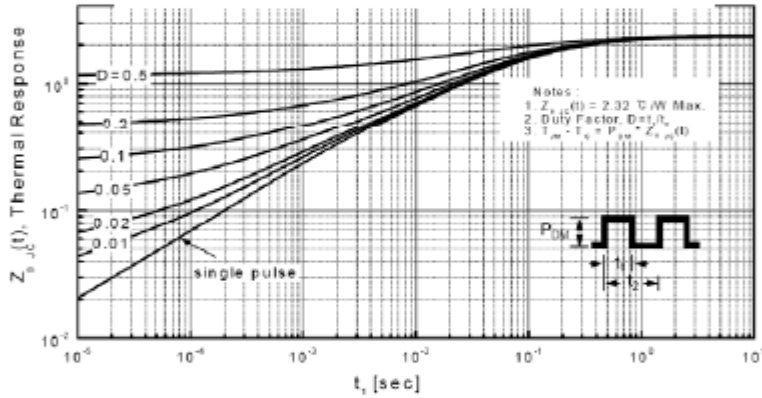


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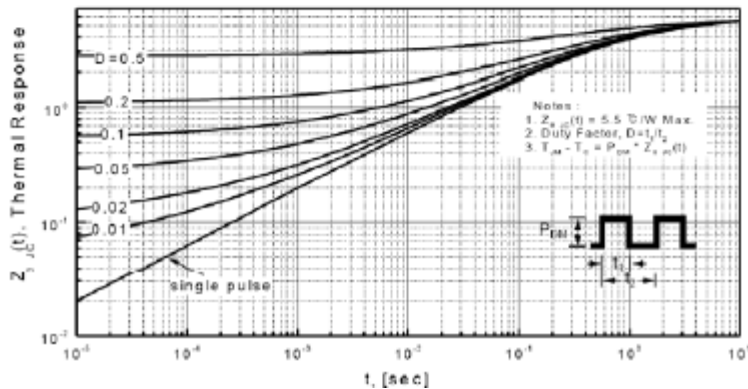
Transient Thermal Response Curve For JCS2N60MB/MFB



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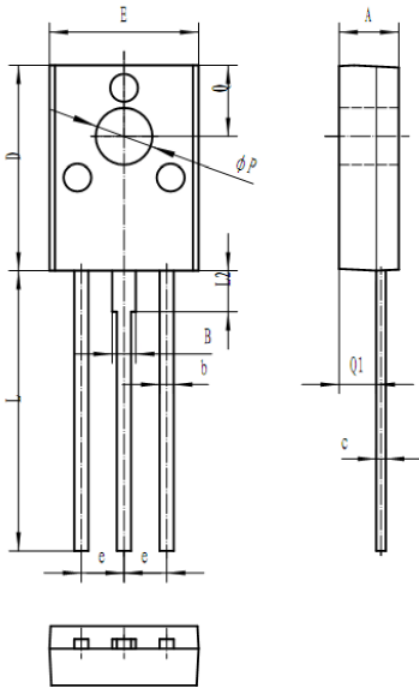




外形尺寸 PACKAGE MECHANICAL DATA

TO-126F

单位 Unit : mm



符号 Symbol	尺寸 (mm) Size (mm)
A	3.10-3.30
B	1.22-1.47
b	0.60-0.90
c	0.45-0.70
D	10.50-11.20
E	7.50-8.50
e	2.29TYP
Q	3.60-4.00
Q1	1.80-2.20
L	15-00-16.00
L2	2.10-2.30
P	2.95-3.15

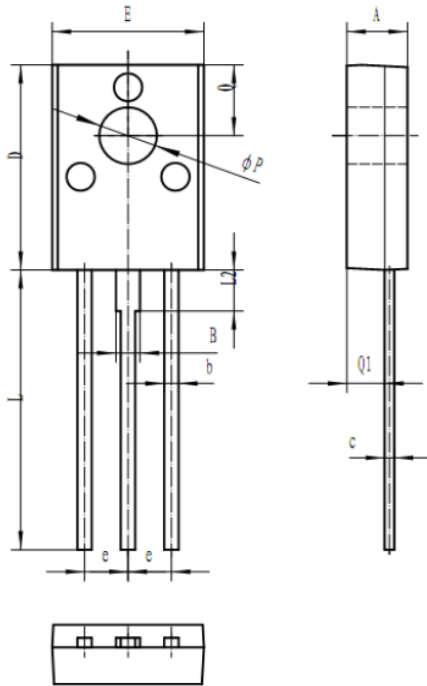
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2. We strongly recommend customers check carefully on the trademark when buying our product, if there is any question, please



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